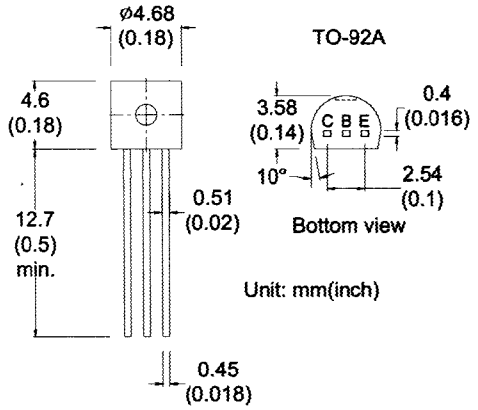
MICRO ELECTRONICS

CL5770

NPN SILICON TRANSISTOR

DESCRIPTION

CL5770 is NPN silicon planar epitaxial transistor designed for small signal high frequency amplifiers and



ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	30V
Collector-Emitter Voltage	VCEO	15V
Emitter-Base Voltage	VEBO	3V
Collector Current	IC	50mA
Total Power Dissipation	Ptot	300mW
Operating Junction & Storage Temperature	Tj, Tstg	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS	
Collector-Base Breakdown Voltage	BVCBO	30		V	IC=0.1mA	IE=0
Collector-Emitter Breakdown Voltage	LVCEO*	15		V	IC=3mA	IB=0
Emitter-Base Breakdown Voltage	BVEBO	3		V	IE=0.01mA	IC=0
Collector Cutoff Current	ICBO		10	nA	VCB=15V	IE=0
D.C. Current Gain	HFE*	60	120		IC=3mA	VCE=1V
Collector-Emitter Saturation Voltage	VCE(sat)		0.4	V	IC=10mA	IB=1mA
Base-Emitter Saturation Voltage	VBE(sat)		1	V	IC=10mA	IB=1mA
Gain Bandwidth Product	fT	800	TYP	MHz	IC=8mA	VCE=10V
					f=100MHz	
Output Capacitance	Cob		1.7	pF	VCB=10V	f=1MHZ
Input Capacitance	Cib		2	pF	VEB=0.5V	f=1MHZ
Noise Figure	NF		6	dB	IC=1mA	VCE=6V
					RG=400ohm	f=60MHZ

* Pulse test : pulse width <300μS, duty cycle < 2%.

MICRO ELECTRONICS LTD.
38, Hung To Road, Microtron Bulding, Kwun Tong, Kowloon, Hong Kong.
Kwun Tong P.O. Box 69477 Hong Kong. Fax No. 2341 0321 Telex:43510 Micro Hx. Tel: 2343 0181-5